



STS9P2UH7 Information



For Reference Only

Part Number STS9P2UH7

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 20V 9A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STS9P2UH7 Specifications

Manufacturer Part NumberSTS9P2UH7ManufacturerSTMicroelectronicsCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackage8-SOIC (0.154", 3.90mm Width)SeriesSTripFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ IdIV @ 250µAGate Charge (Qg) (Max) @ Vgs22nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds2390pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)2.7W (Tc)Rds On (Max) @ Id, Vgs22.5 mOhm @ 4.5A, 4.5VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series STripFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 22nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2390pF @ 16V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 2.7W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 4.5A, 4.5V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	STS9P2UH7
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Package 8-SOIC (0.154", 3.90mm Width) Series STripFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4.5V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 22nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2390pF @ 16V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 2.7W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 4.5A, 4.5V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
Series STripFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 22nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2390pF @ 16V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 2.7W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 4.5A, 4.5V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds2390pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)2.7W (Tc)Rds On (Max) @ Id, Vgs22.5 mOhm @ 4.5A, 4.5VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds2390pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)2.7W (Tc)Rds On (Max) @ Id, Vgs22.5 mOhm @ 4.5A, 4.5VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	STripFET?
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds2390pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)2.7W (Tc)Rds On (Max) @ Id, Vgs22.5 mOhm @ 4.5A, 4.5VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) 1.5V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) ESV FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 4.5A, 4.5V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 9A (Tc) 9A	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)1.5V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds2390pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)2.7W (Tc)Rds On (Max) @ Id, Vgs22.5 mOhm @ 4.5A, 4.5VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 1V @ 250μA 1V @ 250μA 22nC @ 4.5V 2390pF @ 16V 2390pF @ 16V 2390pF @ 16V 22390pF @ 16V 225 mOhm @ 4.5A, 4.5V 2150°C (TJ) Surface Mount Supplier Device Package 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	9A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2390pF @ 16V Vgs (Max) ±8V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 4.5A, 4.5V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	1.5V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max)±8VFET Feature-Power Dissipation (Max)2.7W (Tc)Rds On (Max) @ Id, Vgs22.5 mOhm @ 4.5A, 4.5VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	22nC @ 4.5V
FET Feature - Power Dissipation (Max) 2.7W (Tc) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 4.5A, 4.5V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	2390pF @ 16V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22.5 mOhm @ 4.5A, 4.5V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs22.5 mOhm @ 4.5A, 4.5VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.7W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	22.5 mOhm @ 4.5A, 4.5V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

STS9P2UH7 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STS9P2UH7 Payment Methods



















STS9P2UH7 Shipping Methods













If you have any question about STS9P2UH7, please do not hesitate to contact us!

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